Product Preview

High-Linearity 3.3 pF Passive Tunable Integrated Circuits (PTIC)

Introduction

ON Semiconductor's PTICs have excellent RF performance and power consumption, making them suitable for any mobile handset or radio application. The fundamental building block of our PTIC product line is a tunable material called ParaScan™, based on Barium Strontium Titanate (BST). PTICs have the ability to change their capacitance from a supplied bias voltage generated by the Control IC. TCP−5133UA has higher linearity for use in applications which require improved harmonic performance. The 3.3 pF ultra-high tuning, high Q PTICs are available as wafer-level chip scale packages (WLCSP).

Key Features

- Ultra-High Tuning Range (5:1) and Operation up to 24 V
- Usable Frequency Range: from 700 MHz to 2.7 GHz
- High Quality Factor (Q) for Low Loss
- High Power Handling Capability
- Compatible with PTIC Control ICs from ON Semiconductor
- These devices are Pb-Free and RoHS Compliant

Typical Applications

- Multi-band, Multi-standard, Advanced and Simple Mobile Phones
- Tunable Antenna Matching Networks
- Tunable RF Filters
- Active Antennas

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.



ON Semiconductor®

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WLCSP3 0.772x0.993 CASE 567WS

MARKING DIAGRAM

dYW

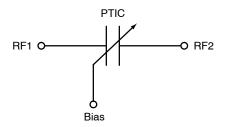
d = Specific Device Code

Y = Year

W = Work Week

Pin#1 marking can be either dot or bar

FUNCTIONAL BLOCK DIAGRAM



PTIC Functional Block Diagram

ORDERING INFORMATION

Device	Package	Shipping [†]		
TCP-5133UA-DT	WLCSP3 (Pb-Free)	7000 Units / 7" Tape & Reel		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

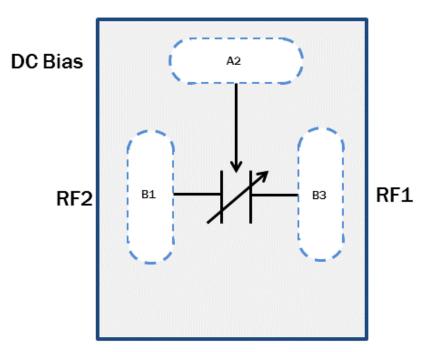


Figure 1. PTIC Functional Block Diagram (Top View)

Table 1. SIGNAL DESCRIPTIONS

Ball / Pad Number	Pin Name	Description
A2	DC Bias 1	DC Bias Voltage
B3	RF1	RF Input
B1	RF2	RF Output

TYPICAL SPECIFICATIONS

Representative Performance Data at 25°C

Table 2. PERFORMANCE DATA

Parameter	Min	Тур	Max	Units
Operating Bias Voltage	1.0		24	V
Capacitance (V _{bias} = 2 V)	3.00	3.30	3.60	pF
Capacitance (V _{bias} = 24 V)	0.59	0.65	0.71	pF
Capacitance Accuracy (V _{bias} = 2-24 V)		9		%
Tuning Range (2 V - 24 V)	4.5	5.1	5.5	
Leakage Current (V _{bias} = 24 V)			4.0	μΑ
Operating Frequency	700		2700	MHz
Quality Factor @ 700 MHz, 2 V (Note 4)	55	70		
Quality Factor @ 700 MHz, 24 V (Note 4)	35	45		
Quality Factor @ 2.7 GHz, 2 V (Note 4)	25	35		
Quality Factor @ 2.7 GHz, 24 V (Note 4)	15	25		
IP3 (V _{bias} = 2 V) (Notes 1, 3, 4)		70		dBm
IP3 (V _{bias} = 24 V) (Notes 1, 3, 4)		80		dBm
2nd Harmonic (V _{bias} = 2 V) (Notes 2, 3, 4)		-74	-67	dBm
2nd Harmonic (V _{bias} = 24 V) (Notes 2, 3, 4)		-80	-75	dBm
3rd Harmonic (V _{bias} = 2 V) (Notes 2, 3, 4)		-60	-55	dBm
3rd Harmonic (V _{bias} = 24 V) (Notes 2, 3, 4)		-90	-85	dBm
Transition Time (Cmin → Cmax) (Note 5)		66		μs
Transition Time (Cmax → Cmin) (Note 5)		48		μs

f₁ = 850 MHz, f₂ = 860 MHz, Pin 25 dBm/Tone
 900 MHz, Pin + 23 dBm
 Harmonics are measured in the reflect configuration in a 50 Ω environment
 Sample testing only. RF_{IN} and RF_{OUT} must be connected to DC ground.
 Sample testing only. PTIC Control IC Turbo Mode must be used.

Representative performance data at 25°C for 3.3 pF WLCSP Package

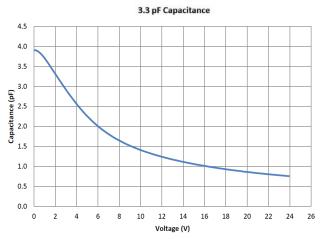


Figure 2. Capacitance

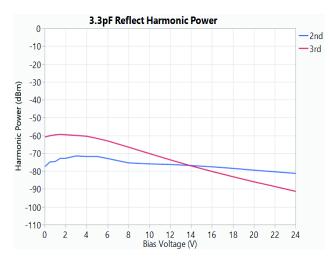


Figure 3. Harmonic Power*

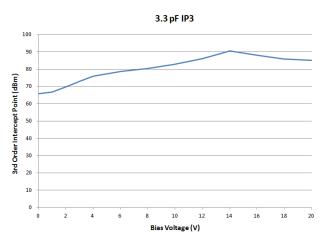


Figure 4. IP3*

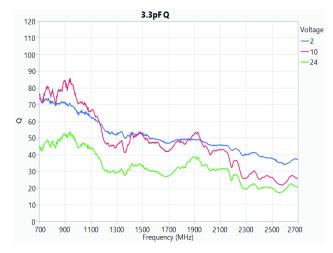


Figure 5. Q*

Table 3. ABSOLUTE MAXIMUM RATINGS

Parameter	Rating	Units
Input Power	+40	dBm
Bias Voltage	+30 (Note 6)	V
Operating Temperature Range	-30 to +85	°C
Storage Temperature Range	-55 to +125	°C
ESD - Human Body Model	Class 1B JEDEC HBM Standard (Note 7)	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 6. WLCSP: Recommended Bias Voltage not to exceed 24 V.
- 7. Class 1B defined as passing 500 V, but may fail after exposure to 1000 V ESD pulse.

^{*}Data shown is representative only.

ASSEMBLY CONSIDERATIONS AND REFLOW PROFILE

The following assembly considerations should be observed:

Cleanliness

These chips should be handled in a clean environment.

Electro-static Sensitivity

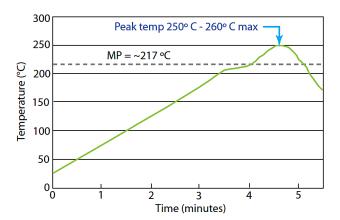
ON Semiconductor's PTICs are ESD Class 1B sensitive. The proper ESD handling procedures should be used.

Mounting

The WLCSP PTIC is fabricated for Flip Chip solder mounting. Connectivity to the RF and Bias terminations on the PTIC die is established through SAC305 solder balls with 90 μ m nominal height (65 μ m to 115 μ m height variation). The PTIC die is RoHS-compliant and compatible with lead-free soldering profile.

Molding

The PTIC die is compatible for over-molding or under-fill.



This reflow profile is a guideline for Pb-free solder materials. Adjustments to this profile are necessary based on specific process requirements and board size, thickness and density. **Not to exceed 260° C for 5 seconds.**

Figure 6. Reflow Profile

ORIENTATION OF THE PTIC FOR OPTIMUM LOSSES

When configuring the PTIC in your specific circuit design, at least one of the RF terminals must be connected to DC ground. If minimum transition times are required, DC ground on both RF terminals is recommended. To minimize losses, the PTIC should be oriented such that RF2 is at the lower RF impedance of the two RF nodes. A shunt PTIC, for example, should have RF2 connected to RF ground.

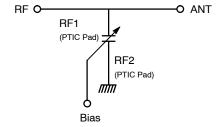


Figure 7. PTIC Orientation Functional Block
Diagram

PART NUMBER DEFINITION

Table 4. PART NUMBERS

	Сарас	Capacitance		king	
Part Number	2 V	24 V	Device ID	Trace Code	Package*
TCP-5133UA-DT	3.30	0.65	d	YW**	3-bump WLCSP

^{*}See PTIC package dimensions on following page.

For information on device numbering and ordering codes, please download the *Device Nomenclature* technical note (TND310/D) from www.onsemi.com.

Table 5. Two Digits Year and Work Week Date coding (YW) - In Process Product / Traceability Date Code Marking

Code	Term	Definition								
YW	Year and Work Week	Two-character Alpha Code. Example: 2005, workweek 10 = GJ								
		YEAR	WORK WEEK	CODE	YEAR	WORK WEEK	CODE	YEAR	WORK WEEK	CODE
		2003	1 26 27 52	CA CZ DA DZ	2004	1 26 27 52	EA EZ FA FZ	2005	1 26 27 52	GA GZ HA HZ
		2006	1 26 27 52	IA IZ JA JZ	2007	1 26 27 52	KA KZ LA LZ	2008	1 26 27 52	MA MZ NA NZ
		2009	1 26 27 52	PA PZ RA RZ	2010	1 26 27 52	SA SZ TA TZ	2011	1 26 27 52	UA UZ VA VZ
		2012	1 26 27 52	WA WZ XA XZ	2013	1 26 27 52	YA YZ ZA ZZ	2014	1 26 27 52	AA AZ BA BZ
		2015	1 26 27 52	CA CZ DA DZ	2016	1 26 27 52	EA EZ FA FZ	2017	1 26 27 52	GA GZ HA HZ

For dates outside of the table: the first character of the code is incremented at the start of workweek 01 and workweek 27 each year. The second character begins with "A" in workweek 01 of each year and increments weekly. "A" follows "Z" to make the code continuous.

^{**}Refer to table below (Table 5) for YW trace code.

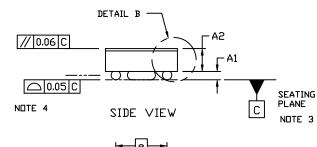
PACKAGE DIMENSIONS

WLCSP3, 0.993x0.772

CASE 567WS ISSUE O

NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DATUM C, THE SEATING PLANE, IS DEFINED BY THE SPHERICAL CROWNS OF THE CONTACTS.
- 4. COPLANARITY APPLIES TO THE SPHERICAL CROWNS OF THE CONTACTS.
- 5. DIMENSIONS 6 AND 61 ARE MEASURED AT THE MAXIMUM CONTACT DIAMETER PARALLEL TO DATUM C. POSITIONAL TOLERANCE APPLIES TO ALL THREE CONTACTS IN BOTH THE X AND Y AXIS.
- 6. BACKSIDE TAPE APPLIED TO IMPROVE PIN 1 MARKING.



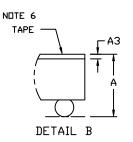
BOTTOM VIEW

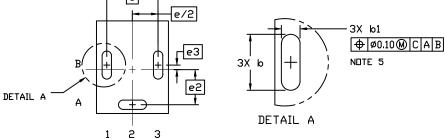
TOP VIEW

PIN A1 REFERENCE A

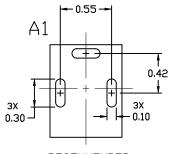
В

D





	MILLIMETERS						
DIM	MIN.	N□M.	MAX.				
Α	0.295	0.335	0.375				
A1	0.065	0.090	0.115				
A2	0.260 REF						
A3	0.025 REF						
b	0.275	0.275 0.300					
b1	0.075	0.100	0.125				
D	0.943	0.993	1.043				
E	0.722	0.772	0.822				
e	0.550 BSC						
e2	0.377 BSC						
e3	0.048 BSC						



RECOMMENDED MOUNTING FOOTPRINT

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TCP-5133UA/D